

Coupled simulation to determine the impact of across wafer variations in oxide PECVD on electrical and reliability parameters of through-silicon vias



E. Baer^{a,*}, P. Evanschitzky^a, J. Lorenz^a, F. Roger^b, R. Minixhofer^b, L. Filipovic^c, R.L. de Orio^c, S. Selberherr^c

^a Fraunhofer IISB, Schottkystrasse 10, 90158 Erlangen, Germany

^b ams AG, Tobelbader Strasse 30, 8141 Unterpremstaetten, Austria

^c Institute for Microelectronics, TU Wien, Gusshausstrasse 27-29/E360, 1040 Wien, Austria

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ABSTRACT

We demonstrate a coupled equipment- and feature-scale process simulation and its application to plasma-enhanced chemical vapor deposition (PECVD) as part of a sequence for the fabrication of a through-silicon via (TSV) interconnect. The TSV structure is characterized electrically and mechanically by means of finite element simulation. This chain allows one to determine the effects of process variations on the electrical and reliability characteristics of the TSV. The simulations predict an across wafer variation of the parasitic DC capacitance between the tungsten metallization and the silicon substrate of about 3%. However, mechanical simulations indicate only a minor influence of the oxide layer thickness variation on the reliability performance of the TSV.

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1. Introduction

Three-dimensional (3D) integration of different semiconductor technologies is a key challenge for the future evolution of enhanced electron devices and systems by increasing the density of components and integrating broader functionality into a single integrated circuit. Through-silicon via (TSV) technology creates a direct electrical path through the entire silicon substrate between, for instance, high-impedance sensors and their associated analog frontend or to a bond/bump pad for stacking to another silicon circuit. Such a structure is generated through a sequence of multiple etching and deposition steps after the CMOS processing including metallization has been completed.

Variability of the processing parameters of these etching and deposition steps, including the variability across the wafer, leads to changes of key TSV geometry parameters such as aspect ratio and thicknesses of deposited layers which strongly influence the electrical and reliability properties of the TSV. In this work, a coupled equipment- and feature-scale process simulation and its

application to layer deposition as part of a sequence for the fabrication of TSVs is demonstrated. The resulting structures are studied with respect to their electrical characteristics and reliability by means of finite element (FEM) simulations.

2. Modeling of the PECVD process for SiO₂ deposition

Part of the processing sequence studied is the plasma-enhanced chemical vapor deposition (PECVD) of a SiO₂ layer in a capacitively coupled plasma (CCP) reactor. In this work, the profile of the deposited SiO₂ layer and its variation across the wafer is investigated by means of simulation. To model the deposition process it is assumed that the adsorbed TEOS fragments are saturated on the surface and that the process is therefore governed by the local fluxes of oxygen ions and radicals [1]. The equipment modeling of a PECVD reactor containing argon and oxygen has been carried out using the Q-VT [2] software which is based on the plasma process simulator HPEM [3]. The reactor studied is a CCP reactor with the gas showerhead as one electrode at the top and the wafer carrier platen as the other electrode. This configuration leads to a maximum ion concentration in the approximate middle between the two electrodes. In the simulation, each of the two electrodes was

* Corresponding author.

E-mail address: eberhard.baer@iisb.fraunhofer.de (E. Baer).

powered with 100 W using a dual-frequency system with 20 MHz for the showerhead electrode and 4 MHz for the wafer carrier platen electrode. For the simulation, the pressure and the mass flow were set to 40 mTorr and 100 sccm, respectively. The mass flow supplied through the showerhead electrode consists of molecular oxygen (95%) and argon (5%). The most important species for the deposition process to be considered in the feature-scale simulation are the oxygen radicals and O_2^+ ions. As an example, Fig. 1 shows the simulated reactor along with the concentration of the O_2^+ ions. Fig. 2 shows the fluxes of oxygen radicals and O_2^+ ions at the substrate versus the distance from the reactor center axis. These fluxes are provided as a boundary condition for feature-scale modeling.

In order to simulate profile evolution on the feature scale, a phenomenological model [4] is employed which describes the local deposition rate R as a composition of contributions from neutrals and ions:

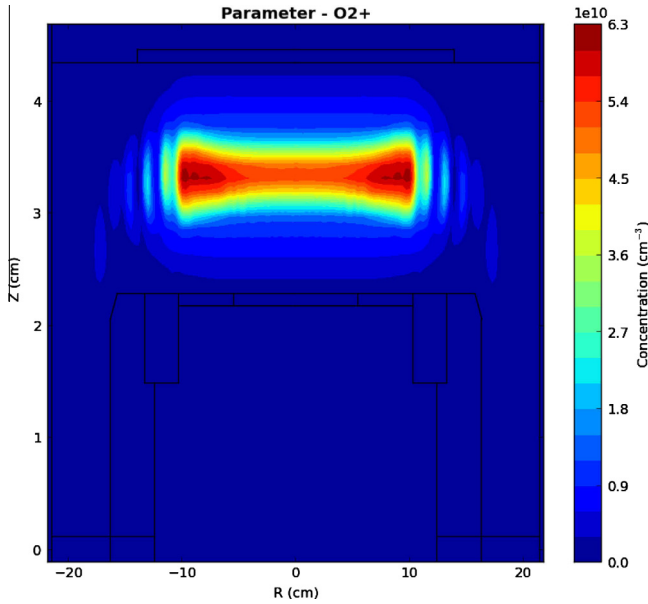


Fig. 1. Equipment simulation result (O_2^+ ions) for a PECVD reactor. The total mass flow and the pressure are 100 sccm and 40 mTorr, respectively. The electrical power (dual-frequency) is 200 W. The substrate (200 mm wafer) is placed on top of the block in the center of the figure. Please note the different scales on R and Z axis which have been chosen for better visualization. The black lines in the figure denote the geometry of the reactor, showing the showerhead electrode at the top and the wafer carrier platen in the middle. For the simulation, a rotationally symmetric geometry has been assumed, a cross section of which is shown in the figure.

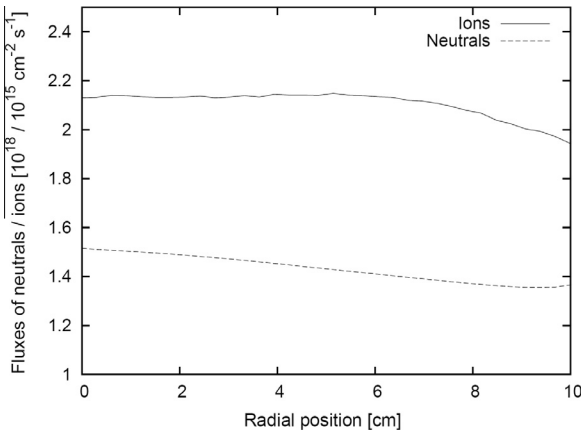


Fig. 2. Fluxes of oxygen neutrals (radicals) and O_2^+ ions at the substrate versus distance from the center axis for the equipment simulation shown in Fig. 1.

$$R \sim s_c F_{\text{neutral}} + F_{\text{ion}} \quad (1)$$

where s_c , F_{neutral} , and F_{ion} are the sticking coefficient of the neutrals, the flux of the neutrals, and the flux of the ions, respectively. The parameters of the model are the relative contribution r of the neutrals to the growth rate in planar sections, the sticking coefficient of the neutrals, and the standard deviation σ of the angular distribution of the ions. In the model [4], separate paths leading to deposition due to the interaction of the surface with neutrals and ions are assumed.

The model is implemented into the in-house tool DEP3D [5]. Due to the absence of actual rate and profile data, for the position on the center axis of the reactor (at 0.0 cm) a typical feature-scale model parameter set ($r = 0.8$, $s_c = 0.15$, $\sigma = 0.1$) according to literature [4] has been used. This can be justified by the fact that this work focuses on the across wafer variations of the model parameters rather than on their absolute values. The variations of the fluxes allow one to determine the variation of the feature-scale model parameters when varying the feature position on the wafer and to simulate the resulting profiles. The variation of the model parameter r can be calculated according to:

$$r = \frac{1}{1 + k_r \frac{F_{\text{ion}}}{F_{\text{neutral}}}}, \quad (2)$$

where k_r is a parameter which needs to be determined for a given position, for instance the center of the wafer, by imposing a value for r . The parameter k_r does not vary with varying fluxes, as it is a constant depending only on the proportionality constants according to Eq. (1). In other words, the logic train is as follows: the typical parameter r as mentioned above is assumed for the position at the center of the wafer. The fluxes F_{ion} and F_{neutral} as determined by equipment simulation allow the calculation of k_r according to Eq. (2). Since k_r is constant, the variations of the fluxes F_{ion} and F_{neutral} across the wafer allow one to calculate the variation of r across the wafer according to Eq. (2).

Additionally, the changes of the growing thickness when varying the feature position on the wafer can be determined according to:

$$R = k_{\text{rate}}(F_{\text{neutral}} + k_r F_{\text{ion}}), \quad (3)$$

where R is the thickness growing in one-dimensional regions of the structure. k_{rate} is a model parameter which does not depend on the fluxes [4]. Therefore, using Eq. (3) the relative changes of the growth rate can be ascertained by determining the changes of the fluxes F_{neutral} and F_{ion} .

As an example, the simulated profiles of a layer deposited by oxide PECVD are shown in Fig. 3. In order to determine the variations of the model parameters, the typical parameter set mentioned above ($r = 0.8$, $s_c = 0.15$, $\sigma = 0.1$) has been assigned to the position at the center of the wafer. Using Eqs. (2) and (3), the changes of r and R across the wafer have been calculated. For instance, for a position at the wafer rim (radial position of 10 cm), a value for r of 0.8 and a growing thickness which is equal to 0.9 times the growing thickness at the center of the wafer are obtained. Therefore, for the example studied here, the profile change is due to the change of the growing thickness rather than due to the change of the conformality (governed by the parameter r in addition to s_c which is assumed to be independent of the local fluxes). For other reactor configurations leading to different variations of the fluxes of neutral and ions across the wafer, this behavior can differ.

To study the impact of the changes of the PECVD oxide profile on the electrical and reliability performance, a process sequence for the fabrication of a TSV structure [6] has been studied. The simulated TSV geometry relies on 2D/3D simulations (with the assumption of rotational symmetry) as shown in Fig. 4. It should

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